



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

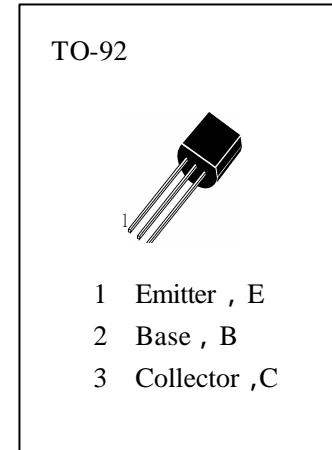
HX789A

APPLICATIONS

Motor drivers.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	—Storage Temperature.....	-55~150
T_j	—Junction Temperature.....	150
P_c	—Collector Dissipation.....	1.5W
V_{CBO}	—Collector-Base Voltage.....	-25V
V_{CEO}	—Collector-Emitter Voltage.....	-25V
V_{EBO}	—Emitter-Base Voltage.....	-5V
I_c	—Collector Current.....	-3A



ELECTRICAL CHARACTERISTICS ($T_a=25$)

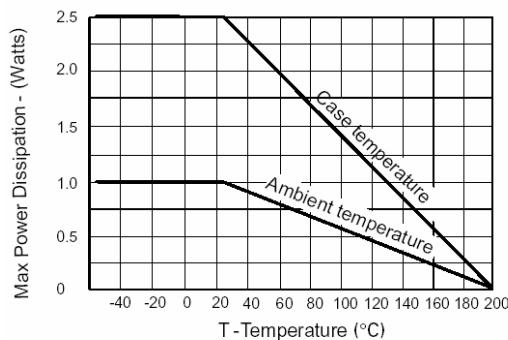
Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-25			V	$I_c=-100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	-25			V	$I_c=-10mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	-5			V	$I_E=-100 \mu A, I_c=0$
ICBO	Collector Cut-off Current			-0.1	μA	$V_{CB}=-15V, I_E=0$
IEBO	Emitter Cut-off Current			-0.1	μA	$V_{EB}=-4V, I_c=0$
HFE	DC Current Gain	250		490		$V_{CE}=-2V, I_c=-1A$
VCE(sat1)	Collector- Emitter Saturation Voltage			-0.25	V	$I_c=-1A, I_B=-10mA$
VCE(sat2)				-0.45	V	$I_c=-2A, I_B=-20mA$
VCE(sat3)				-0.5	V	$I_c=-3A, I_B=-100mA$
VBE(sat)	Base-Emitter Saturation Voltage			-1.0	V	$I_c=-1A, I_B=-10mA$
VBE(on)	Base-Emitter On Voltage		-0.8		V	$V_{CE}=-2V, I_c=-1A$
ft	Current Gain-Bandwidth Product	100			MHz	$V_{CE}=-5V, I_c=-50mA, f=50MHz$
Cob	Output Capacitance		25		pF	$V_{CB}=-10V, I_E=0, f=1MHz$



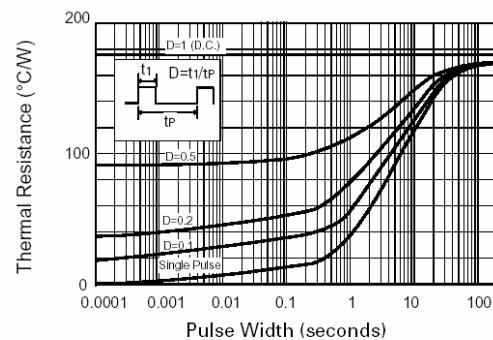
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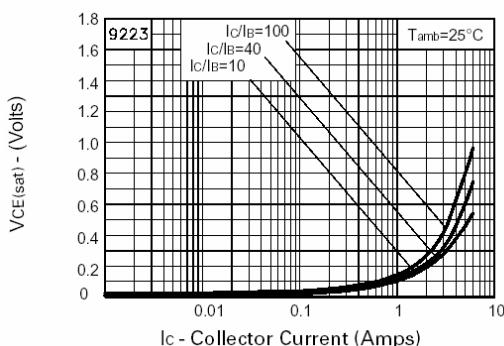
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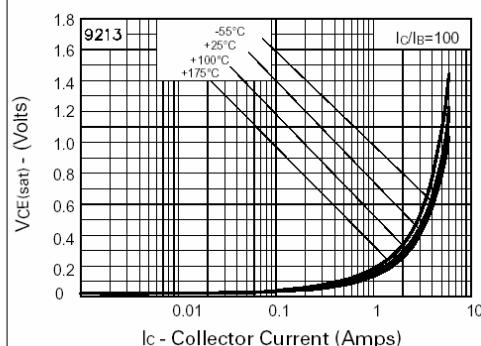
Derating curve



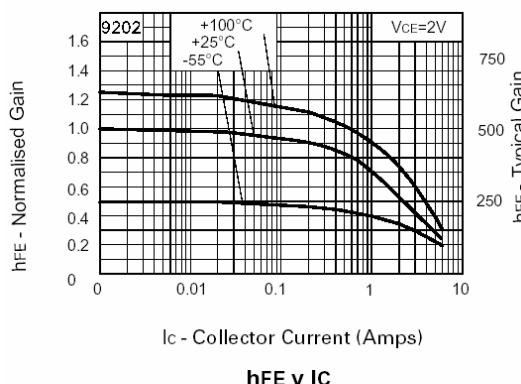
Maximum transient thermal impedance



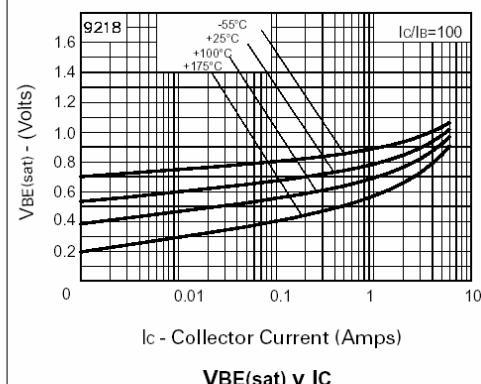
V_{CE(sat)} v IC



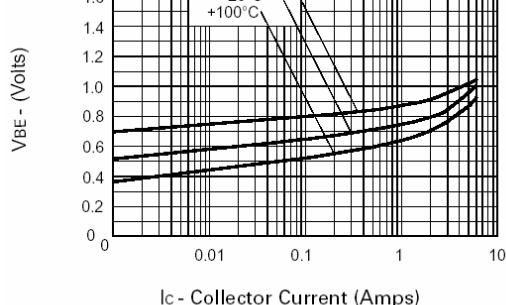
V_{CE(sat)} v IC



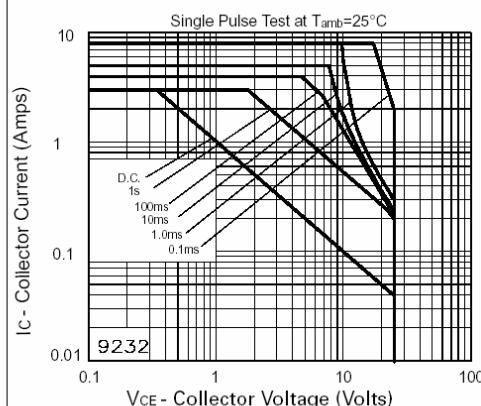
h_{FE} v IC



V_{BE(sat)} v IC



V_{BE(on)} v IC



Safe Operating Area